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PATENT
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Klaus Florian Schuegraf et al.

Examiner: O Nadav

Serial No.: 08/902,809

Group Art Unit: 2811

Filed: July 30, 1997

Docket: 303.278US1

Title: SELECTIVE SPACER TO PREVENT METAL OXIDE FORMATION
DURING POLYCIDE REOXIDATION

AMENDMENT AND RESPONSE

Assistant Commissioner for Patents
Washington, D.C. 20231

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In response to the Office Action dated January 11, 1999, Applicants respectfully request that the Examiner consider and enter the following amendments and remarks in connection with the above-identified patent application.

IN THE CLAIMS

Please cancel claims 32-35.

Please amend the claims as follows:

23. (Amended) A semiconductor device comprising:

an oxide [active area] layer;
at least one feature over the oxide [active area] layer, the feature having a surface and being contiguous with the oxide [active area] layer at a boundary; and
a spacer comprising silicon nitride or an amorphous silicon film covering the surface of the feature and terminating at the boundary wherein the spacer is not in contact with the oxide [active area] layer.

24. (Amended) The semiconductor device of claim 23 wherein:

the feature comprises an electrode including polysilicon, a refractory metal, and a dielectric, or undoped silicon;

[the spacer comprises silicon nitride or an amorphous silicon film;] and
the surface of the feature comprises sidewalls of the electrode.